



BUK762R0-40E

N-channel TrenchMOS standard level FET

28 July 2016

Product data sheet

1. General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|--|-----|-----|------|-----|------|
| V _{DS} | drain-source voltage | T _J ≥ 25 °C; T _J ≤ 175 °C | | - | - | 40 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; Fig. 2 | [1] | - | - | 120 | A |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; Fig. 1 | | - | - | 293 | W |
| Static characteristics | | | | | | | |
| R _{DS(on)} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _J = 25 °C; Fig. 11 | | - | 1.65 | 2 | mΩ |
| Dynamic characteristics | | | | | | | |
| Q _{GD} | gate-drain charge | V _{GS} = 10 V; I _D = 25 A; V _{DS} = 32 V; Fig. 13 ; Fig. 14 | | - | 33.4 | - | nC |

[1] Continuous current is limited by package.

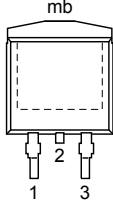
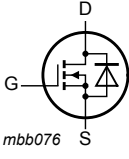


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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|---|---|
| 1 | G | gate |  D2PAK (SOT404) |  mbb076 |
| 2 | D | drain | | |
| 3 | S | source | | |
| mb | D | mounting base; connected to drain | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|--------------|---------|--|---------|
| | Name | Description | Version |
| BUK762R0-40E | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|--------------|--------------|
| BUK762R0-40E | BUK762R0-40E |

8. Limiting values

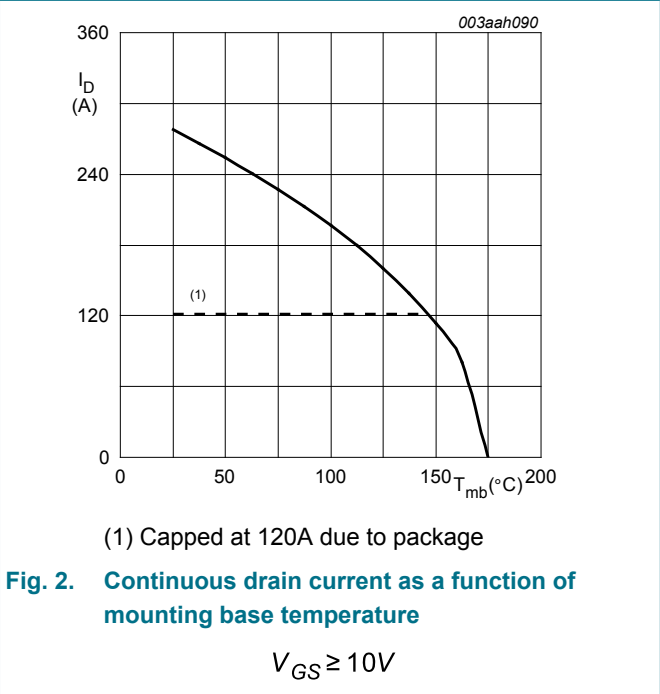
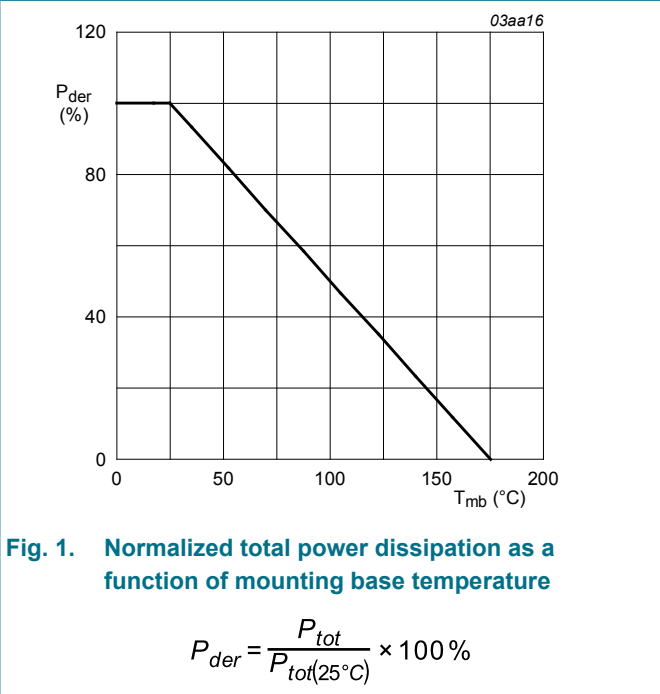
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|-----------|-------------------------|---|---------------------|-----|------|--------------------|
| V_{DS} | drain-source voltage | $T_j \geq 25\text{ }^{\circ}\text{C}$; $T_j \leq 175\text{ }^{\circ}\text{C}$ | | - | 40 | V |
| V_{DGR} | drain-gate voltage | $R_{GS} = 20\text{ k}\Omega$ | | - | 40 | V |
| V_{GS} | gate-source voltage | $T_j \leq 175\text{ }^{\circ}\text{C}$; DC | | -20 | 20 | V |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ }^{\circ}\text{C}$; Fig. 1 | | - | 293 | W |
| I_D | drain current | $T_{mb} = 25\text{ }^{\circ}\text{C}$; $V_{GS} = 10\text{ V}$; Fig. 2 | [1] | - | 120 | A |
| | | $T_{mb} = 100\text{ }^{\circ}\text{C}$; $V_{GS} = 10\text{ V}$; Fig. 2 | [1] | - | 120 | A |
| I_{DM} | peak drain current | $T_{mb} = 25\text{ }^{\circ}\text{C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Fig. 3 | | - | 1110 | A |
| T_{stg} | storage temperature | | | -55 | 175 | $^{\circ}\text{C}$ |
| T_j | junction temperature | | | -55 | 175 | $^{\circ}\text{C}$ |

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|--|--------|-----|------|------|
| Source-drain diode | | | | | | |
| I _S | source current | T _{mb} = 25 °C | [1] | - | 120 | A |
| I _{SM} | peak source current | pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C | | - | 1110 | A |
| Avalanche ruggedness | | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I _D = 120 A; V _{sup} ≤ 40 V; R _{GS} = 50 Ω; V _{GS} = 10 V; T _{j(init)} = 25 °C; unclamped; Fig. 4 | [2][3] | - | 621 | mJ |

- [1] Continuous current is limited by package.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.



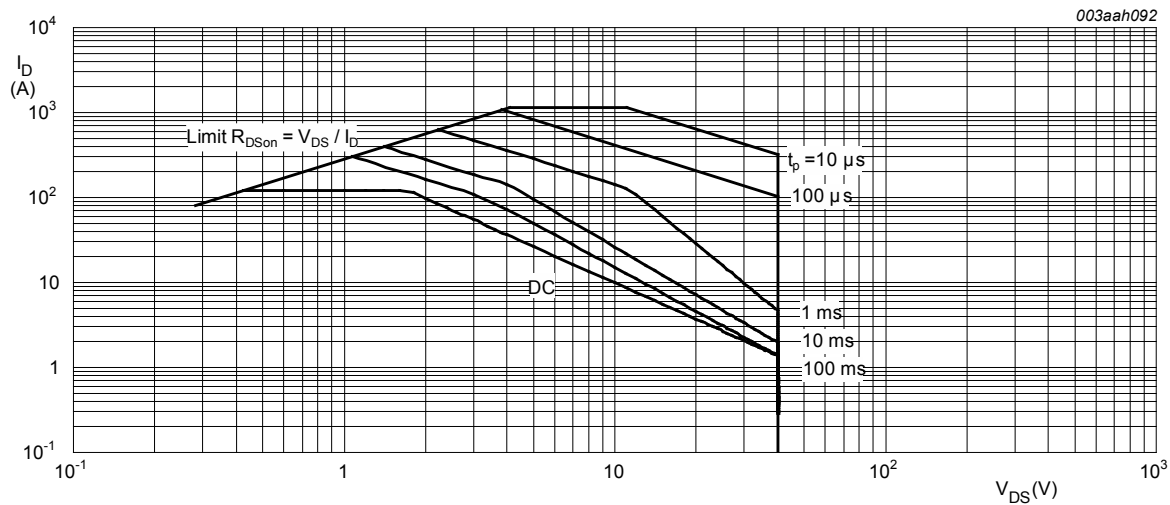


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}\text{C}$; I_{DM} is a single pulse

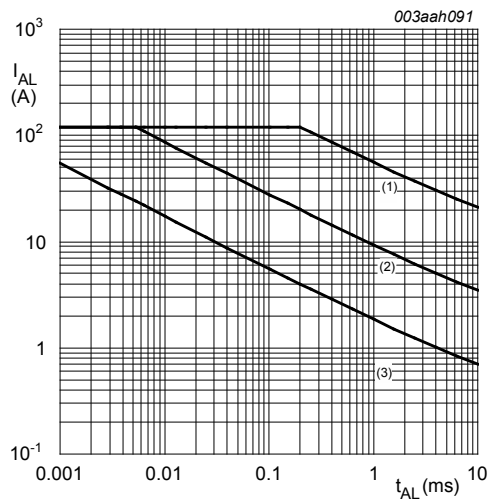


Fig. 4. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j\text{(init)}} = 25^{\circ}\text{C}$; (2) $T_{j\text{(init)}} = 150^{\circ}\text{C}$; (3) Repetitive Avalanche

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|---|---|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5 | - | - | 0.51 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | minimum footprint; mounted on a printed-circuit board | - | 50 | - | K/W |

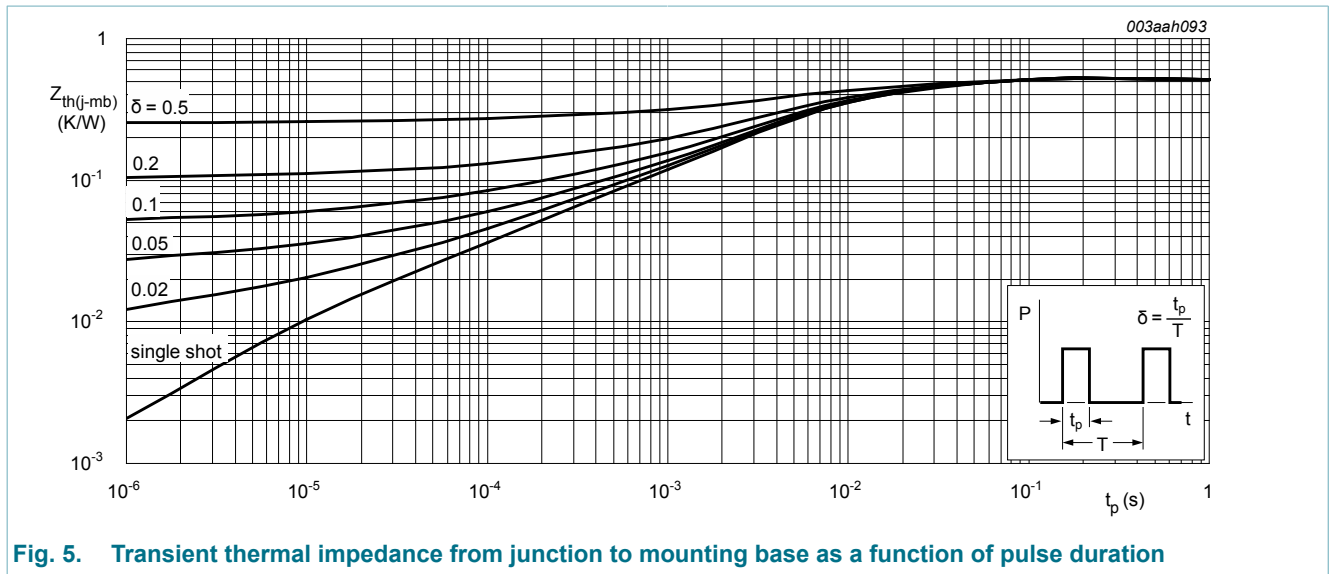


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|-------------------------|----------------------------------|---|--|-----|-------|-----|---------------|
| Static characteristics | | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 250\text{ }\mu\text{A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$ | | 40 | - | - | V |
| | | $I_D = 250\text{ }\mu\text{A}; V_{GS} = 0\text{ V}; T_j = -55\text{ }^\circ\text{C}$ | | 36 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1\text{ mA}; V_{DS} = V_{GS}; T_j = 25\text{ }^\circ\text{C};$ Fig. 9; Fig. 10 | | 2.4 | 3 | 4 | V |
| | | $I_D = 1\text{ mA}; V_{DS} = V_{GS}; T_j = -55\text{ }^\circ\text{C};$ Fig. 10 | | - | - | 4.5 | V |
| | | $I_D = 1\text{ mA}; V_{DS} = V_{GS}; T_j = 175\text{ }^\circ\text{C};$ Fig. 10 | | 1 | - | - | V |
| I_{DSS} | drain leakage current | $V_{DS} = 40\text{ V}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$ | | - | 0.36 | 3 | μA |
| | | $V_{DS} = 40\text{ V}; V_{GS} = 0\text{ V}; T_j = 175\text{ }^\circ\text{C}$ | | - | - | 500 | μA |
| I_{GSS} | gate leakage current | $V_{GS} = 20\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$ | | - | 2 | 100 | nA |
| | | $V_{GS} = -20\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$ | | - | 2 | 100 | nA |
| R_{DSon} | drain-source on-state resistance | $V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 11 | | - | 1.65 | 2 | m Ω |
| | | $V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 175\text{ }^\circ\text{C};$ Fig. 12; Fig. 11 | | - | - | 3.8 | m Ω |
| Dynamic characteristics | | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $I_D = 25\text{ A}; V_{DS} = 32\text{ V}; V_{GS} = 10\text{ V};$ Fig. 13; Fig. 14 | | - | 109.2 | - | nC |
| Q_{GS} | gate-source charge | | | - | 27.5 | - | nC |
| Q_{GD} | gate-drain charge | | | - | 33.4 | - | nC |

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------------------|------------------------------|---|-----|------|------|------|
| C_{iss} | input capacitance | $V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^{\circ}\text{C};$ Fig. 15 | - | 6250 | 8500 | pF |
| C_{oss} | output capacitance | | - | 1210 | 1450 | pF |
| C_{rss} | reverse transfer capacitance | | - | 605 | 840 | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS} = 30\text{ V}; R_L = 1.2\text{ }\Omega; V_{GS} = 10\text{ V};$ $R_{G(ext)} = 5\text{ }\Omega$ | - | 29 | - | ns |
| t_r | rise time | | - | 36 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 79 | - | ns |
| t_f | fall time | | - | 46 | - | ns |
| L_D | internal drain inductance | from upper edge of drain mounting base to center of die | - | 2.5 | - | nH |
| L_S | internal source inductance | from source lead to source bonding pad | - | 7.5 | - | nH |
| Source-drain diode | | | | | | |
| V_{SD} | source-drain voltage | $I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C};$ Fig. 16 | - | 0.79 | 1.2 | V |
| t_{rr} | reverse recovery time | $I_S = 20\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$ $V_{DS} = 25\text{ V}$ | - | 43 | - | ns |
| Q_r | recovered charge | | - | 54 | - | nC |

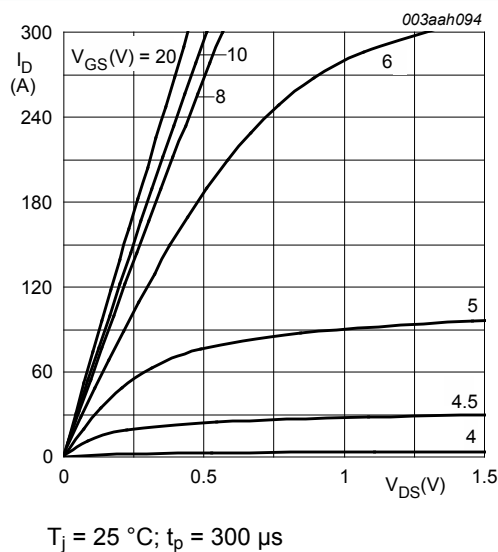


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

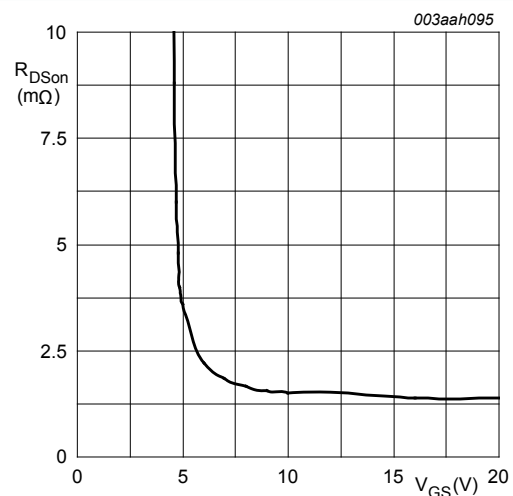


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\text{ }^{\circ}\text{C}; I_D = 25\text{ A}$

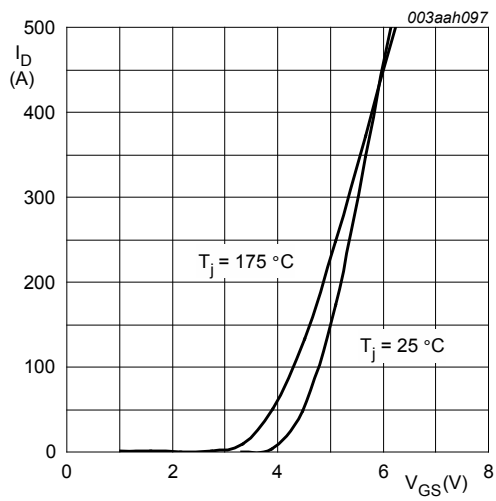


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10V$

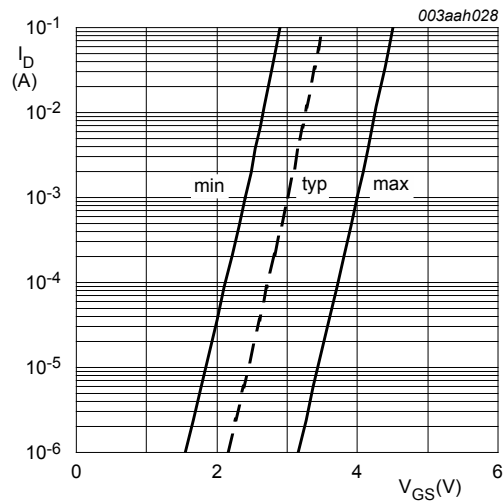


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

$T_J = 25^{\circ}C; V_{DS} = 5V$

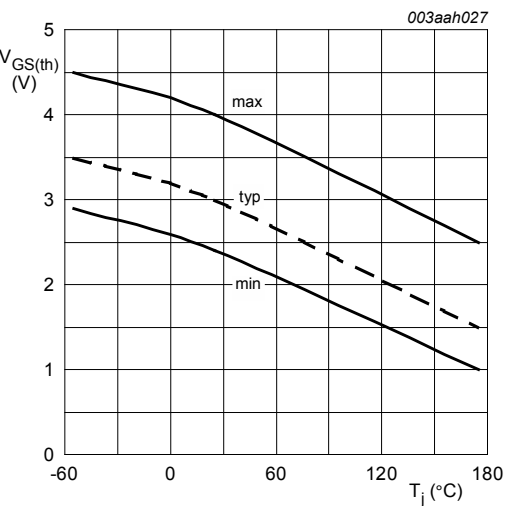


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

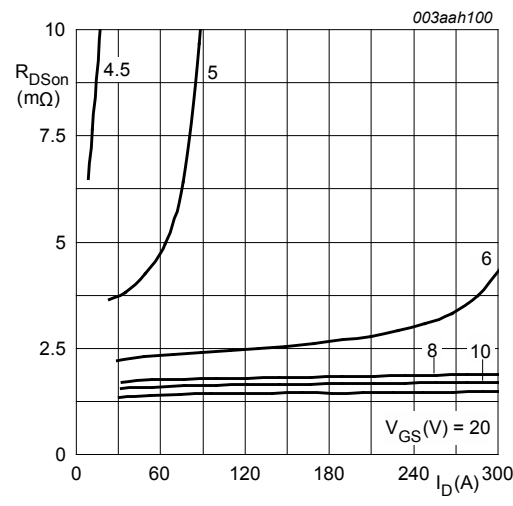


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

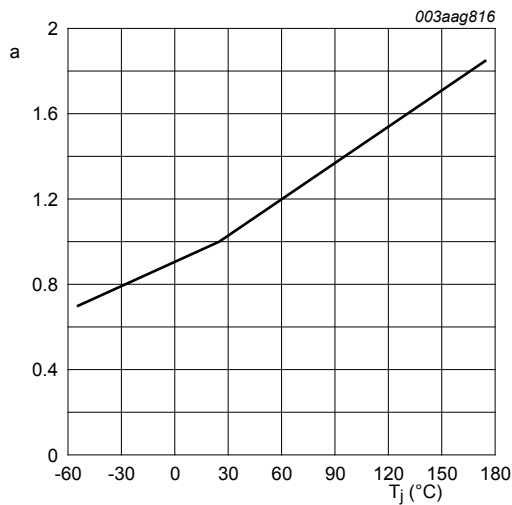


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}\text{C})}$$

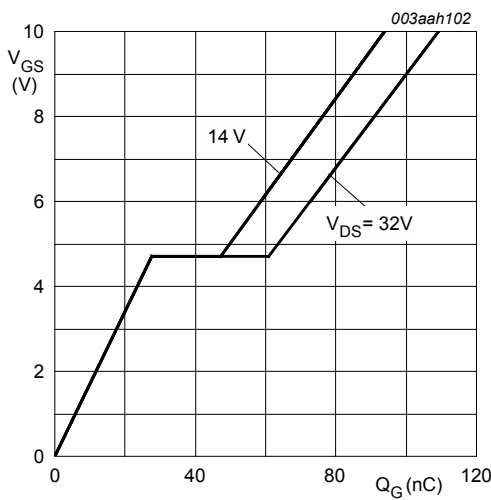


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}\text{C}; I_D = 25\text{ A}$$

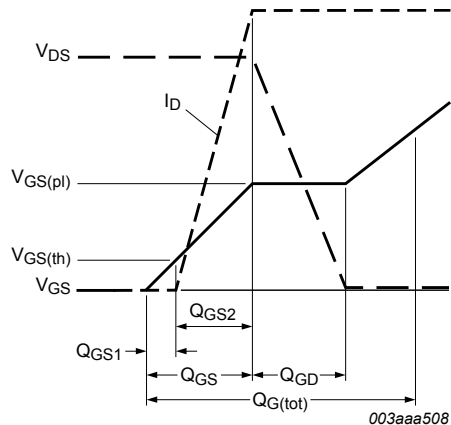


Fig. 13. Gate charge waveform definitions

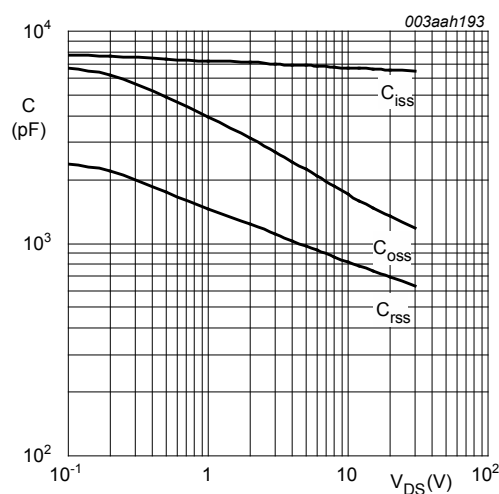


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$$

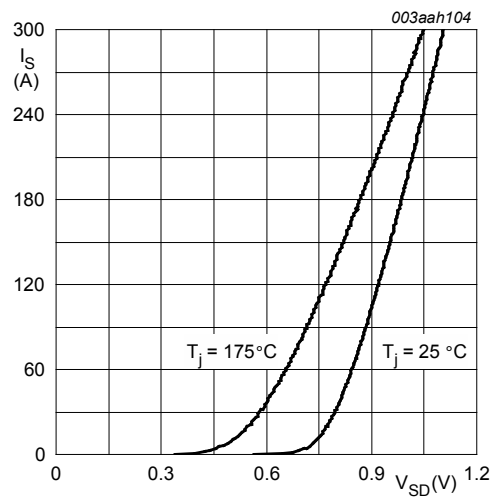


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values
 $V_{GS} = 0V$

11. Package outline

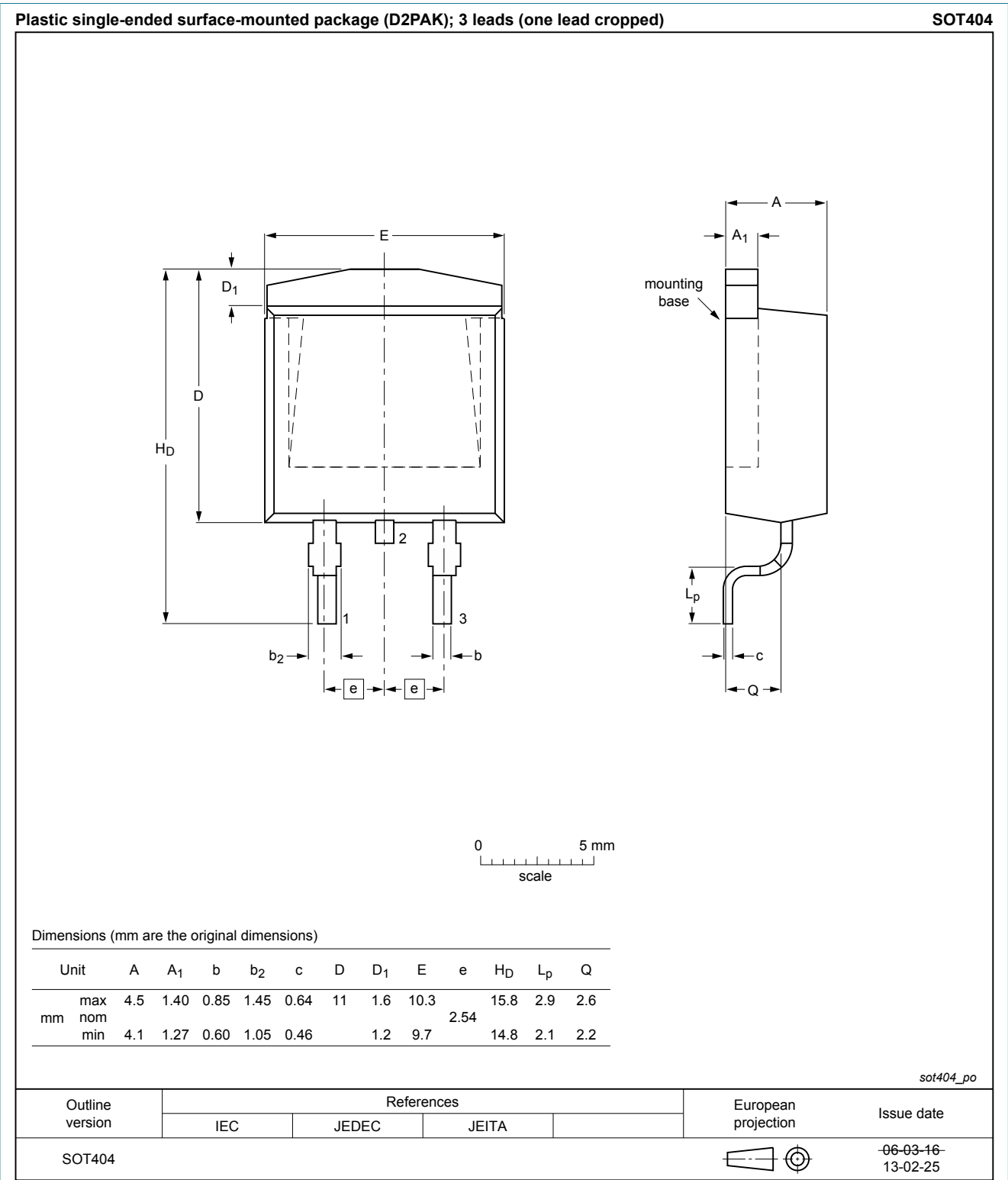


Fig. 17. Package outline D2PAK (SOT404)

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|--------------------------------|--------------------|---|
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